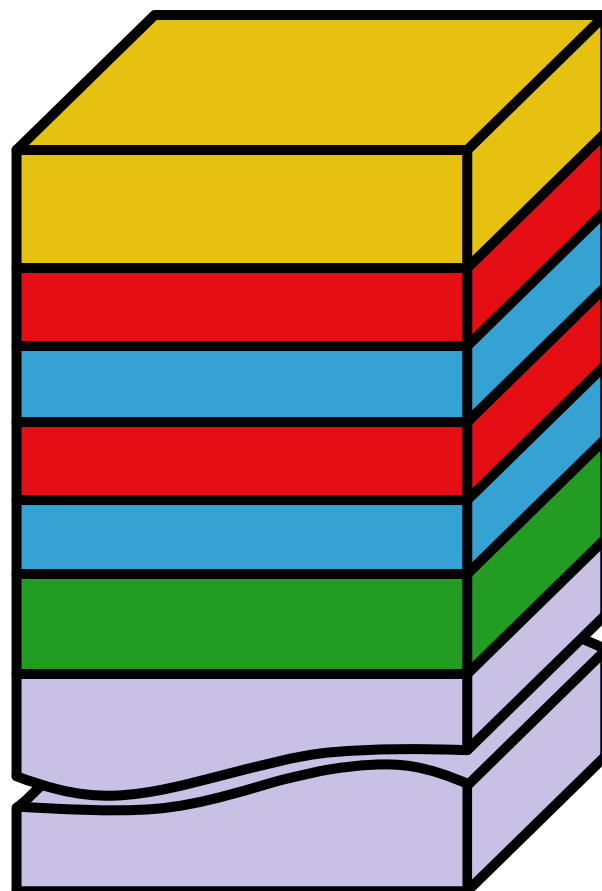


<...> (250°C)

AlAs барьер  
Ga<sub>1-x</sub>Mn<sub>x</sub>As яма  
AlAs

Ga<sub>1-x</sub>Mn<sub>x</sub>As  
buffer GaAs  
330 nm

GaAs (001)



30  
перио-  
дов

| обр  | FMQ1 | FMQ2 | FMQ3 |
|------|------|------|------|
| d(я) | 10   | 10   | 5    |
| d(б) | 3    | 3    | 3    |
| x, % | 2.5  | 4    | 2.5  |

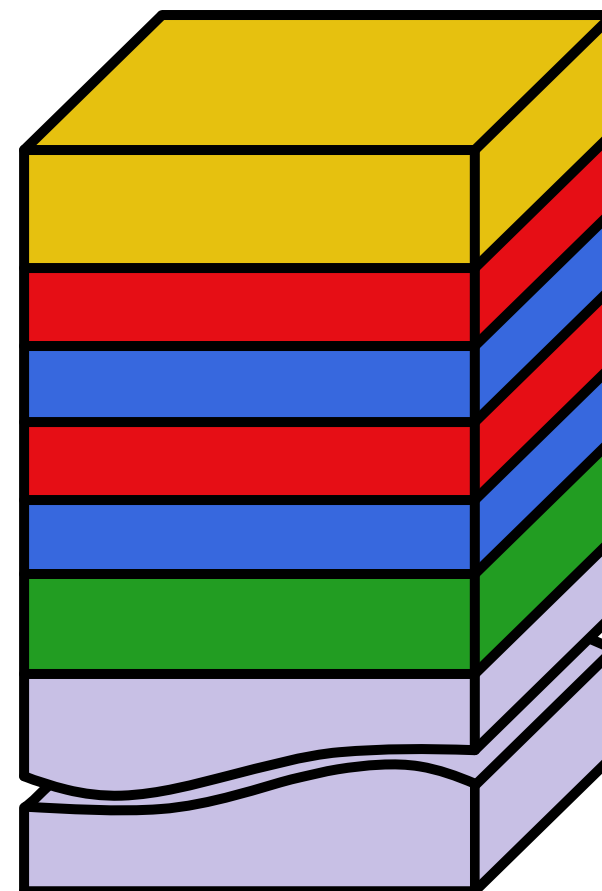
FMQ1/2/3 (MBE)

<...> (560°C)

AlAs барьер  
GaAs:Mn яма  
AlAs

GaAs:Mn  
buffer GaAs  
330 nm

GaAs (001)



30  
перио-  
дов

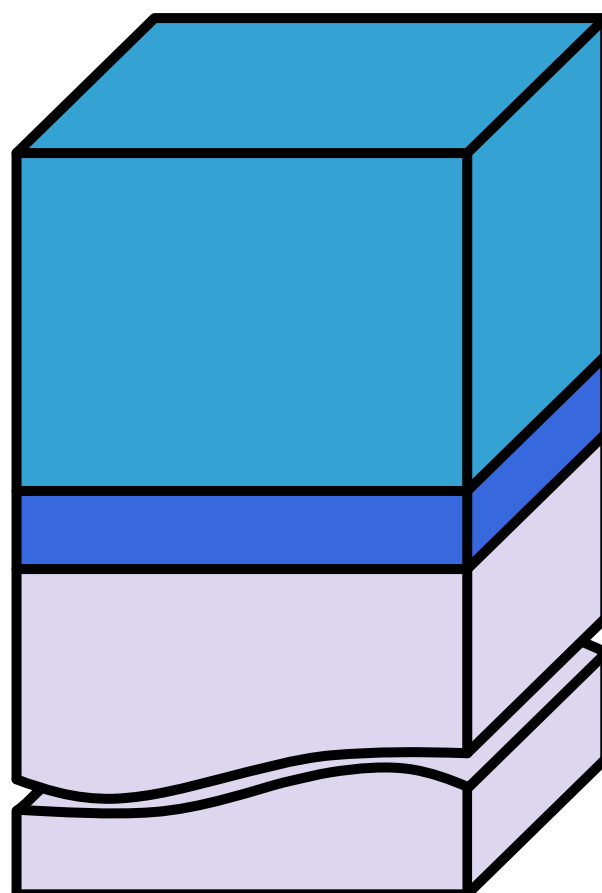
| обр  | DQ1                  | DQ2 |
|------|----------------------|-----|
| d(я) | 10                   | 5   |
| d(б) | 6                    | 3   |
| x, % | 2.5x10 <sup>-5</sup> |     |

DQ1/2 (MBE)

(Ga,Mn)As  
T<sub>g</sub>=250°C  
1000 nm  
Mn:4%

buffer GaAs  
T<sub>g</sub>=600°C  
100 nm

GaAs (001)

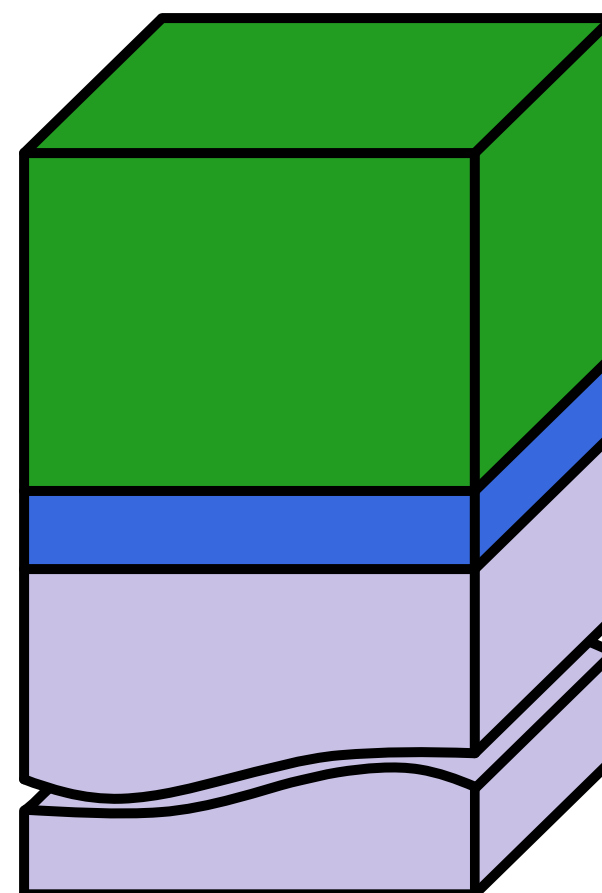


FMB (MBE)

GaAs:Mn  
T<sub>g</sub>=560°C  
1000 nm  
Mn:3x10<sup>17</sup> cm<sup>-3</sup>

buffer GaAs  
T<sub>g</sub>=600°C  
100 nm

GaAs (001)



R1 (MBE)